

SSDM 2007 Time Table

Wednesday, September 19										
Main Convention Hall										
10:00-12:30 PL: Opening Session/SSDM Award										
Room 101 (A)	Room 102 (B)	Room 201A (C)	Room 201B (D)	Room 202A (E)	Room 202B (F)	Room 303 (G)	Room 304 (H)	Room 405 (I)	Room 406 (J)	Multi-Purpose Hall (K)
14:00-15:50 Area 1: Advanced Gate Stack /Si Processing Science A-1: Metal Gate-I	14:00-16:00 Area 3: CMOS Devices/Device Physics B-1: Ge, SiGe Channel Transistor Technology	14:00-15:50 Area 2: Characterization and Materials Engineering for Interconnect Integration C-1: Novel Interconnects	14:00-15:50 Area 5: Advanced Circuits and Systems D-1: Scaling and Circuit Design Concern	14:00-16:00 Area 7: Photonic Devices and Device Physics E-1: Quantum-Dot Devices	14:00-16:00 Area 8: Advanced Material Synthesis and Crystal Growth Technology F-1: Compound Semiconductors	14:00-16:00 Area 6: Compound Semiconductor Circuits, Electron Devices and Device Physics G-1: GaN FETs I	14:00-16:00 Area 10: Organic Materials Science, Device Physics, and Applications H-1: Organic Photo-Electronics	14:00-16:00 Area 9: Physics and Applications of Novel Functional Materials and Devices I-1: Novel Si Transistors	14:00-15:50 Area 4: Advanced Memory Technology J-1: DRAM I	
16:15-18:15 Area 1: Advanced Gate Stack /Si Processing Science A-2: Ge MIS	16:15-18:25 Area 3: CMOS Devices/Device Physics B-2: Transport in Nanoscale MOSFETs	16:15-17:30 Area 12: Spintronic Materials and Devices C-2: Spintronic Materials and Quantum Structures	16:15-18:15 Area 11: Micro/Nano Electromechanical and Bio-Systems (Devices) D-2: MEMS Technology	16:15-18:15 Area 7: Photonic Devices and Device Physics E-2: Special Session: Photonic Crystals and Si Photonics I	16:15-17:30 Area 8: Advanced Material Synthesis and Crystal Growth Technology F-2: Oxides	16:15-18:00 Area 6: Compound Semiconductor Circuits, Electron Devices and Device Physics G-2: GaN FETs II	16:15-18:00 Area 10: Organic Materials Science, Device Physics, and Applications H-2: Organic Light Emitting Devices	16:15-18:00 Area 9: Physics and Applications of Novel Functional Materials and Devices I-2: Transport Through Novel Materials and Structures	16:15-17:45 Area 4: Advanced Memory Technology J-2: Flash Memory I	
18:30-20:30 Banquet/Paper Award & Young Researcher Award (Multi-Purpose Hall 1F)										
Thursday, September 20										
Room 101 (A)	Room 102 (B)	Room 201A (C)	Room 201B (D)	Room 202A (E)	Room 202B (F)	Room 303 (G)	Room 304 (H)	Room 405 (I)	Room 406 (J)	Multi-Purpose Hall (K)
9:00-10:30 Area 1: Advanced Gate Stack /Si Processing Science A-3: Reliability-I	9:00-10:30 Area 3: CMOS Devices/Device Physics B-3: CMOS Integration	9:00-10:30 Area 2: Characterization and Materials Engineering for Interconnect Integration C-3: Plasma Induced Damage of Low-k Materials	9:00-10:20 Area 5: Advanced Circuits and Systems D-3: RF Components	9:00-10:30 Area 7: Photonic Devices and Device Physics E-3: Special Session: Photonic Crystals and Si Photonics II	9:00-10:15 Area 8: Advanced Material Synthesis and Crystal Growth Technology F-3: Group-IV Semiconductors I	9:00-10:15 Area 6: Compound Semiconductor Circuits, Electron Devices and Device Physics G-3: High-Speed Devices and ICs I	9:00-10:30 Area 13: Applications of Nanotubes and Nanowires H-3: Nanowire & Nanotube Sensors		9:00-10:20 Area 4: Advanced Memory Technology J-3: Flash Memory II	(Poster setting)
10:45-12:15 Short Presentation Area 1	10:45-12:15 Short Presentation Area 3	10:45-12:15 Short Presentation Area 2 and Area 12	10:45-12:15 Short Presentation Area 5 and Area 11	10:45-12:15 Short Presentation Area 7	10:45-12:15 Short Presentation Area 8	10:45-12:15 Short Presentation Area 6	10:45-12:15 Short Presentation Area 10 and Area 13	10:45-12:15 Short Presentation Area 9	10:45-12:15 Short Presentation Area 4	
13:00-15:00 Poster Session (Multi-Purpose Hall 1F)										
15:15-16:25 Area 1: Advanced Gate Stack /Si Processing Science A-5: Junction	15:15-16:35 Area 3: CMOS Devices/Device Physics B-5: Mobility Characterization	15:15-16:45 Area 12: Spintronic Materials and Devices C-5: Symposium on Magnetic Tunnel Junctions and Beyond	15:15-16:15 Area 5: Advanced Circuits and Systems D-5: RF CMOS Circuits and Systems	15:15-16:30 Area 7: Photonic Devices and Device Physics E-5: Special Session: Photonic Crystals and Si Photonics III	15:15-16:30 Area 8: Advanced Material Synthesis and Crystal Growth Technology F-5: Group-IV Semiconductors II	15:15-16:15 Area 6: Compound Semiconductor Circuits, Electron Devices and Device Physics G-5: High-Speed Devices and ICs II	15:15-16:30 Area 13: Applications of Nanotubes and Nanowires H-5: Nanowire Growth and Devices I		15:15-16:25 Area 4: Advanced Memory Technology J-5: PRAM	(Poster removed by 18:00)
16:45-18:05 Area 1: Advanced Gate Stack /Si Processing Science A-6: Reliability-II	16:45-18:05 Area 3: CMOS Devices/Device Physics B-6: Device Technology	17:00-18:00 Area 12: Spintronic Materials and Devices C-6: Symposium on Magnetic Tunnel Junctions and Beyond		16:45-18:00 Area 7: Photonic Devices and Device Physics E-6: Detectors and Sensors	16:45-17:45 Area 8: Advanced Material Synthesis and Crystal Growth Technology F-6: Group-IV Semiconductors III	16:45-18:00 Area 6: Compound Semiconductor Circuits, Electron Devices and Device Physics G-6: Process and Characterization	16:45-17:45 Area 13: Applications of Nanotubes and Nanowires H-6: Nanowire Growth and Devices II		16:45-17:55 Area 4: Advanced Memory Technology J-6: ReRAM	
18:30-20:30 Rump Session Room 101(A) "Oxide Electronics -Status and Outlook-" Room 102(B) "New Materials meet Advanced Silicon Technology"										
Friday, September 21										
Room 101 (A)	Room 102 (B)	Room 201A (C)	Room 201B (D)	Room 202A (E)	Room 202B (F)	Room 303 (G)	Room 304 (H)	Room 405 (I)	Room 406 (J)	Multi-Purpose Hall (K)
9:00-10:30 Area 1: Advanced Gate Stack /Si Processing Science A-7: Metal Gate-II	9:00-10:20 Area 3: CMOS Devices/Device Physics B-7: Stress Enhancement Technologies	9:00-10:30 Area 2: Characterization and Materials Engineering for Interconnect Integration C-7: Interconnects for RF and Mixed Signal Application	9:00-10:30 Area 11: Micro/Nano Electromechanical and Bio-Systems (Devices) D-7: Nano-Bio Devices I	9:00-10:30 Area 7: Photonic Devices and Device Physics E-7: All-Optical Light Control	9:00-10:15 Area 8: Advanced Material Synthesis and Crystal Growth Technology F-7: Material Characterization	9:00-10:30 Area 6: Compound Semiconductor Circuits, Electron Devices and Device Physics G-7: Emerging Devices	9:00-10:30 Area 10: Organic Materials Science, Device Physics, and Applications H-7: Organic Transistor I		9:00-10:20 Area 4: Advanced Memory Technology J-7: DRAM II	
10:45-12:05 Area 1: Advanced Gate Stack /Si Processing Science A-8: High-k/Metal Gate Transistor	10:45-12:25 Area 3: CMOS Devices/Device Physics B-8: Modeling and Simulation	10:45-12:15 Area 2: Characterization and Materials Engineering for Interconnect Integration C-8: Interconnect Reliability	10:45-12:15 Area 11: Micro/Nano Electromechanical and Bio-Systems (Devices) D-8: Nano-Bio Devices II	10:45-12:15 Area 7: Photonic Devices and Device Physics E-8: Lasers and LEDs			10:45-12:15 Area 10: Organic Materials Science, Device Physics, and Applications H-8: Organic Transistor II	10:45-12:00 Area 9: Physics and Applications of Novel Functional Materials and Devices I-8: Novel Nanostructure Devices	10:45-12:05 Area 4: Advanced Memory Technology J-8: FeRAM/MRAM	
13:15-14:55 Area 1: Advanced Gate Stack /Si Processing Science A-9: FUSI	13:15-14:55 Area 3: CMOS Devices/Device Physics B-9: Post Planar CMOS	13:15-15:05 Area 2: Characterization and Materials Engineering for Interconnect Integration C-9: Low-k and Airgap	13:15-14:45 Area 11: Micro/Nano Electromechanical and Bio-Systems (Devices) D-9: Spectroscopy for Bio Sensing	13:15-15:00 Area 7: Photonic Devices and Device Physics E-9: LEDs	13:15-14:55 Area 1: Advanced Gate Stack/Si Processing Science F-9: Characterization	13:15-14:35 Area 5: Advanced Circuits and Systems G-9: Imaging Technology	13:15-14:45 Area 10: Organic Materials Science, Device Physics, and Applications H-9: Organic Transistor III	13:15-15:00 Area 9: Physics and Applications of Novel Functional Materials and Devices I-9: Quantum Dots and Qubits	13:15-15:00 Area 13: Applications of Nanotubes and Nanowires J-9: Carbon Nanotube Devices and Growth I	
	15:15-17:05 Area 3: CMOS Devices/Device Physics B-10: Noise and RF	15:25-16:25 Area 2: Characterization and Materials Engineering for Interconnect Integration C-10: Nanoscale Characterization	15:15-16:45 Area 11: Micro/Nano Electromechanical and Bio-Systems (Devices) D-10: μ -TAS and Medical Applications		15:15-16:35 Area 1: Advanced Gate Stack/Si Processing Science F-10: Advanced Process	15:15-16:35 Area 5: Advanced Circuits and Systems G-10: Connectivity		15:15-16:45 Area 9: Physics and Applications of Novel Functional Materials and Devices I-10: Novel Devices	15:15-16:30 Area 13: Applications of Nanotubes and Nanowires J-10: Carbon Nanotube Devices and Growth II	